



100 V, 2.7 A PNP low V_{CEsat} (BISS) transistor

Rev. 01 — 11 May 2010

Product data sheet

1. Product profile

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

NPN complement: PBSS8510PA.

1.2 Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability

1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-100	V
Ic	collector current		-	-	-2.7	А
Ісм	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	-	-4	A
R _{CEsat}	collector-emitter saturation resistance	I _C = -2.7 A; I _B = -135 mA	<u>[1]</u> -	110	166	mΩ

 $\label{eq:point} \begin{tabular}{ll} \mbox{Pulse test: } t_p \leq 300 \ \mu \mbox{s; } \delta \leq 0.02. \end{tabular}$





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2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline Graph	ic symbol
1	base		
2	emitter	3	3
3	collector		
		1 2	sym013
		Transparent top view	

3. Ordering information

Table 3. Ord	lering infor	mation	
Type number	Package		
	Name	Description	Version
PBSS9410PA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; three terminals; body $2 \times 2 \times 0.65$ mm	SOT1061

4. Marking

Table 4.	Marking codes	
Type num	iber	Marking code
PBSS941	0PA	AG

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

			-		
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	-100	V
V _{CEO}	collector-emitter voltage	open base	-	-100	V
V _{EBO}	emitter-base voltage	open collector	-	-7	V
I _C	collector current		-	-2.7	А
I _{CM}	peak collector current	single pulse; $t_p \leq 1 ms$	-	-4	A
I _B	base current		-	-600	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	500	mW
			[2] _	1	W
			<u>[3]</u>	1.4	W
			[4] _	2.1	W

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Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

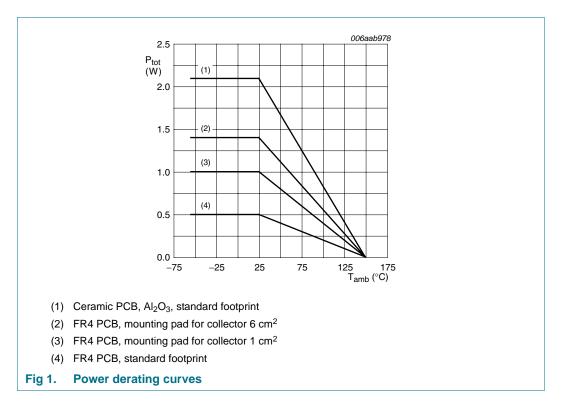
Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



6. Thermal characteristics

Thermal characteristics					
Parameter	Conditions	Min	Тур	Max	Unit
thermal resistance from	in free air	<u>[1]</u> _	-	250	K/W
junction to ambient		[2] _	-	125	K/W
		[3]	-	90	K/W
		[4]	-	60	K/W
	Parameter thermal resistance from	ParameterConditionsthermal resistance fromin free air	ParameterConditionsMinthermal resistance from junction to ambientin free air[1]-[2]-[3]-	ParameterConditionsMinTypthermal resistance from junction to ambientin free air[1][2][3]	ParameterConditionsMinTypMaxthermal resistance from junction to ambientin free air[1]250[2]125[3]90

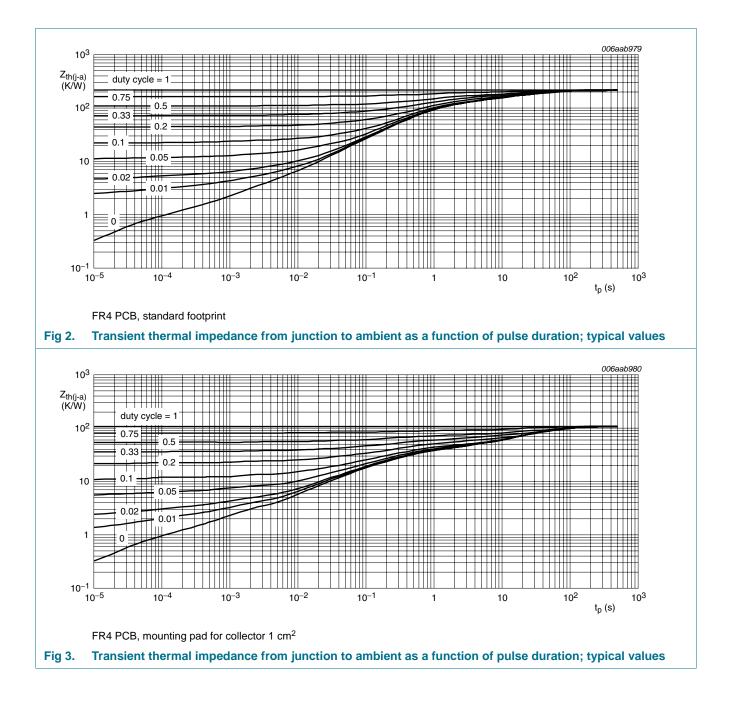
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

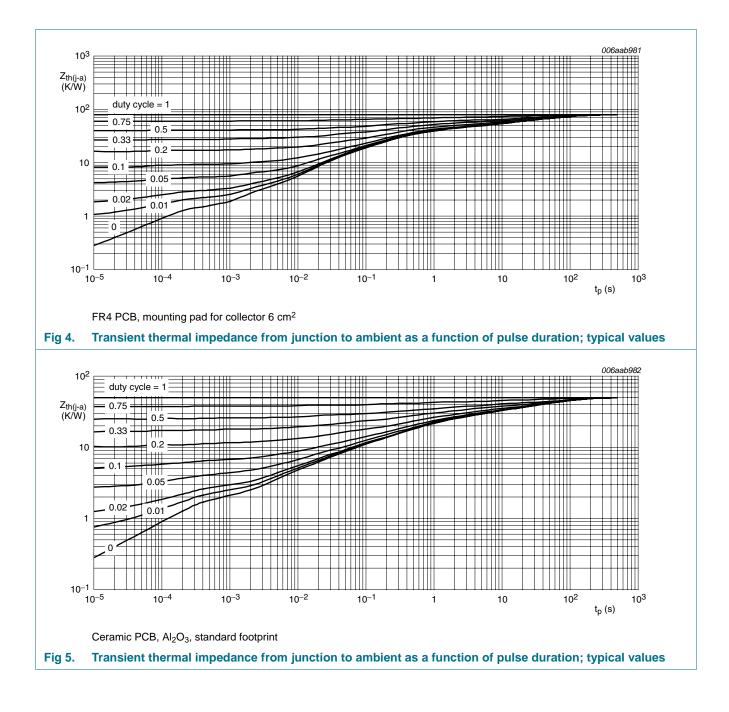
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7. Characteristics

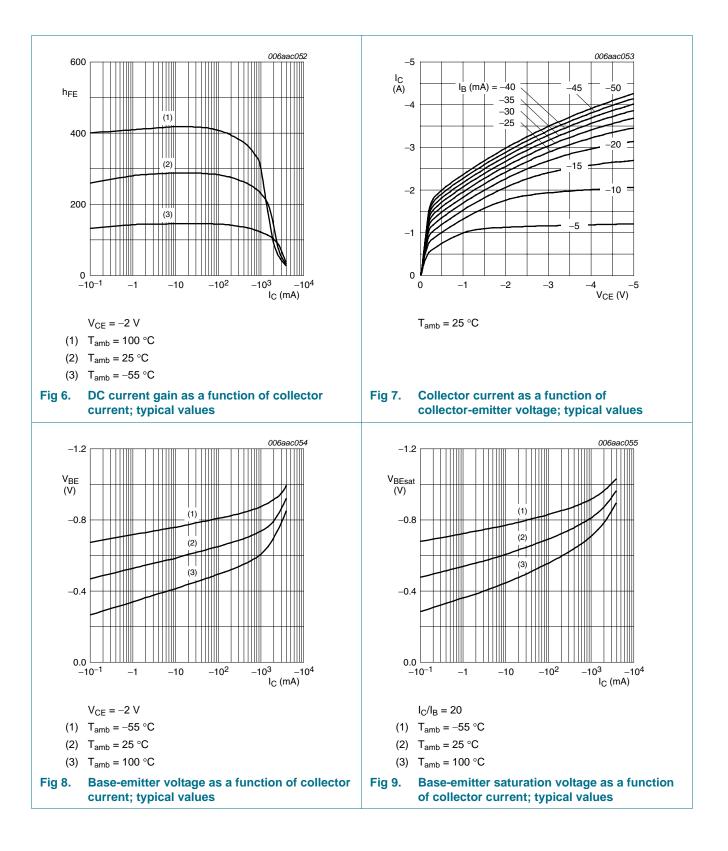
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base	$V_{CB} = -80 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
	cut-off current	$V_{CB} = -80 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	$V_{CE} = -80 \text{ V}; V_{BE} = 0 \text{ V}$	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -2 V$	<u>[1]</u>			
		I _C = -0.5 A	180	295	-	
		I _C = -1 A	170	260	-	
		I _C = -2 A	100	150	-	
		I _C = -3 A	15	25	-	
V _{CEsat}	collector-emitter	$I_{C} = -0.5 \text{ A}; I_{B} = -50 \text{ mA}$	<u>[1]</u> _	-45	-70	mV
	saturation voltage	$I_{C} = -1 \text{ A}; I_{B} = -50 \text{ mA}$	<u>[1]</u> _	-95	-150	mV
		$I_{C} = -2 \text{ A}; I_{B} = -200 \text{ mA}$	<u>[1]</u> _	-125	-185	mV
		$I_{C} = -2.7 \text{ A}; I_{B} = -135 \text{ mA}$	<u>[1]</u> _	-290	-450	mV
R _{CEsat}	collector-emitter saturation resistance	$I_{C} = -2.7 \text{ A}; I_{B} = -135 \text{ mA}$	<u>[1]</u> _	110	166	mΩ
V _{BEsat}	base-emitter	$I_{C} = -1 \text{ A}; I_{B} = -10 \text{ mA}$	<u>[1]</u> _	-0.75	-0.9	V
	saturation voltage	$I_{\rm C}$ = -2.7 A; $I_{\rm B}$ = -135 mA	<u>[1]</u> _	-0.95	-1.1	V
V _{BEon}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -2 \text{ A}$	<u>[1]</u> -	-0.75	-0.9	V
t _d	delay time	V_{CC} = -9 V; I_C = -2 A;	-	17	-	ns
t _r	rise time	$I_{Bon} = -0.1 \text{ A}; I_{Boff} = 0.1 \text{ A}$	-	185	-	ns
t _{on}	turn-on time		-	202	-	ns
t _s	storage time		-	325	-	ns
t _f	fall time		-	190	-	ns
t _{off}	turn-off time		-	515	-	ns
f _T	transition frequency	$V_{CE} = -10 \text{ V};$ $I_{C} = -100 \text{ mA};$ f = 100 MHz	70	115	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	40	50	pF

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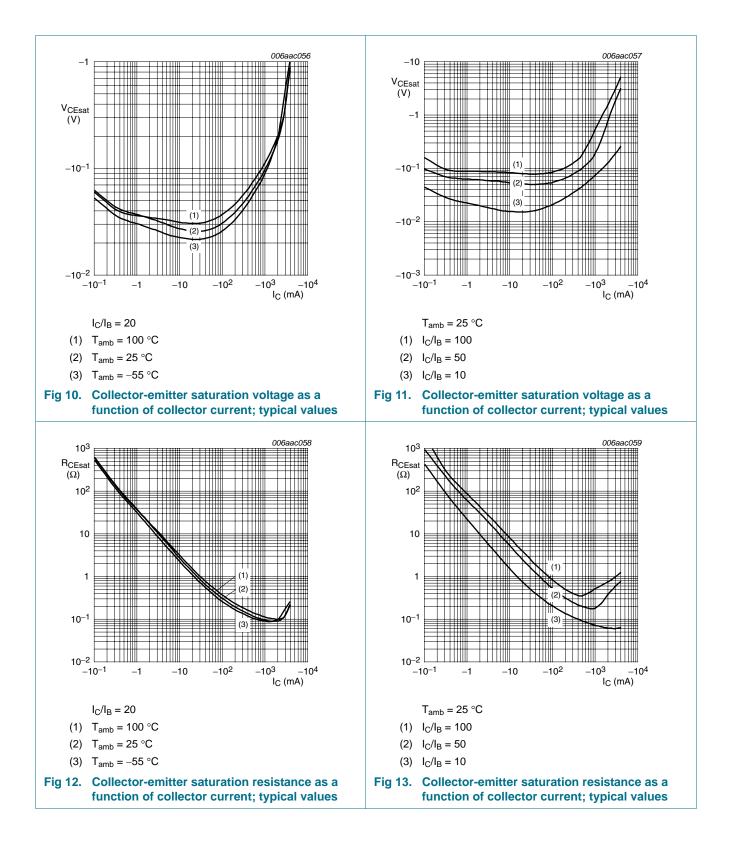
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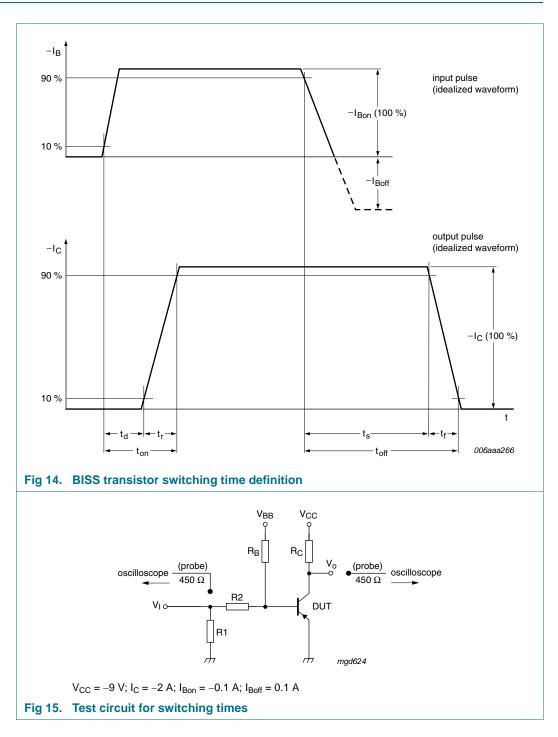
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100 V, 2.7 A PNP low V_{CEsat} (BISS) transistor



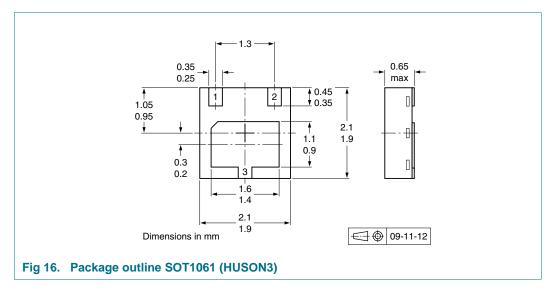
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8. Test information



100 V, 2.7 A PNP low V_{CEsat} (BISS) transistor

9. Package outline



10. Packing information

Table 8. Packing methods

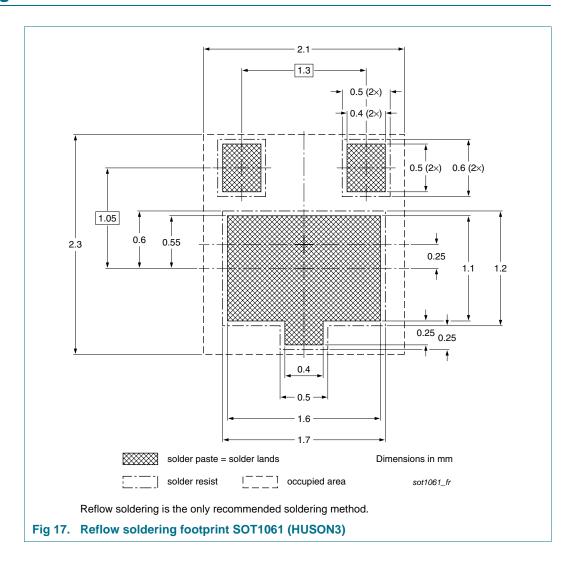
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			3000
PBSS9410PA	SOT1061	4 mm pitch, 8 mm tape and reel	-115

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

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11. Soldering



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12. Revision history

Table 9. Revision hist	Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS9410PA v.1	20100511	Product data sheet	-	-	

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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